

N-channel TrenchMOS SiliconMAX standard level FET Rev. 04 — 14 December 2010 Product de

Product data sheet

Product profile 1.

1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- 1.3 Applications
 - DC-to-DC converters

Suitable for high frequency applications due to fast switching characteristics

Switched-mode power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	200	V
I _D	drain current	T _{mb} = 25 °C	-	-	35	А
P _{tot}	total power dissipation		-	-	250	W
Static cha	aracteristics					
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 17 \text{ A};$ $T_j = 25 \text{ °C}$	-	60	70	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 35 A; V _{DS} = 160 V; T _j = 25 °C	-	28	-	nC

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		<u>_</u>
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbbo76 S

SOT404 (D2PAK)

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information Type number Package Name Description

	Name	Description	Version
PSMN070-200B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

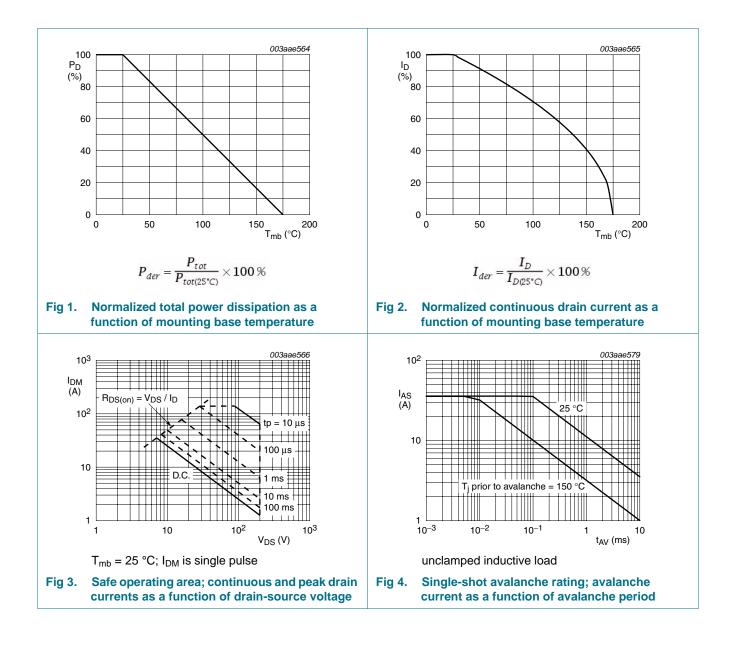
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	200	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	200	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 100 °C	-	25	А
		T _{mb} = 25 °C	-	35	А
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C	-	140	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	250	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	35	А
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	140	А
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{\text{D}} = 35 \text{ A}; \\ V_{sup} \leq 50 \text{ V}; \text{ unclamped}; \text{t}_{p} = 100 \mu\text{s}; \\ R_{GS} = 50 \Omega $	-	462	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 50 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ R _{GS} = 50 Ω ; unclamped	-	35	А

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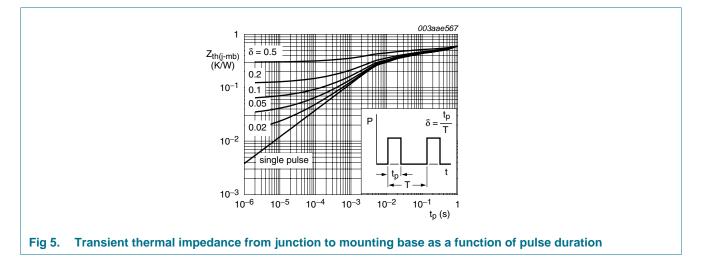
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	0.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board ; minimum footprint	-	50	-	K/W



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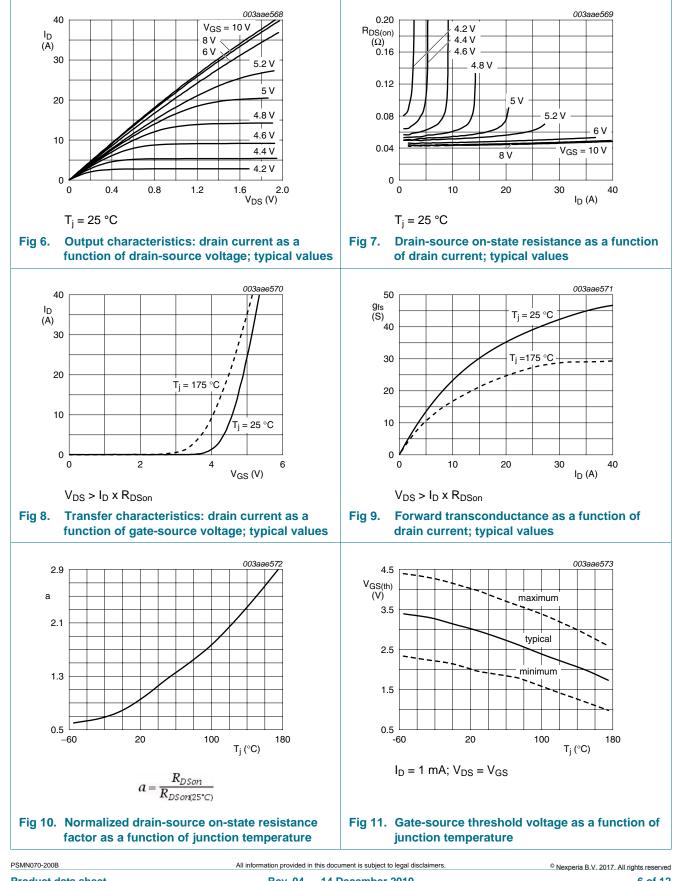
6. Characteristics

Table 6.	Characteristics			_		
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	200	-	-	V	
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	178	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
voltage	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
I _{DSS}	drain leakage current	V_{DS} = 200 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
		$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
	V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 17 A; T _j = 175 °C	-	-	203	mΩ
	resistance	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 17 \text{ A}; \text{ T}_{j} = 25 ^{\circ}\text{C}$	-	60	70	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 35 \text{ A}; V_{DS} = 160 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}$	-	77	-	nC
Q _{GS}	gate-source charge		-	16	-	nC
Q _{GD}	gate-drain charge		-	28	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	4570	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	370	-	pF
C _{rss}	reverse transfer capacitance		-	160	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 100 V; R_L = 2.7 Ω ; V_{GS} = 10 V;	-	22	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \ \Omega; T_j = 25 \ ^{\circ}C$	-	100	-	ns
t _{d(off)}	turn-off delay time		-	80	-	ns
t _f	fall time		-	90	-	ns
L _D	internal drain inductance	measured from tab to centre of die ; $T_j = 25 \ ^\circ C$	-	3.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$	-	160	-	ns
Qr	recovered charge	V _{DS} = 30 V; T _j = 25 °C	-	1	-	μC

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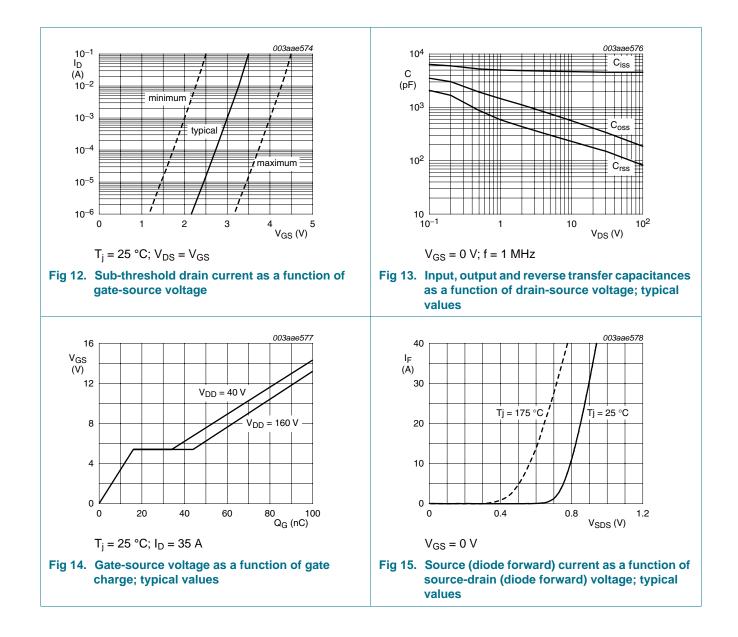
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7. Package outline

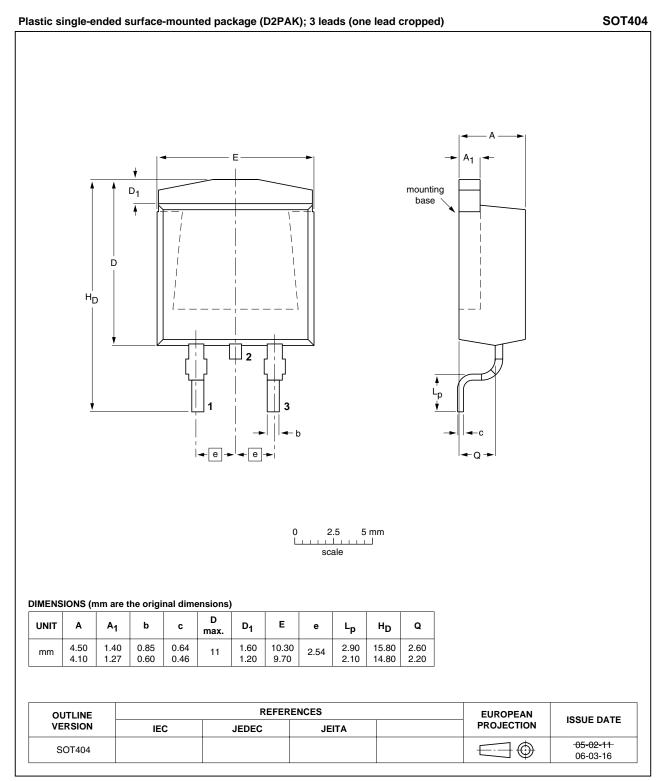


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Release date	Data sheet status	Change notice	Supersedes
20101214	Product data sheet	-	PSMN070-200_SERIES_HG v.3
		•	to comply with the new identity
 Legal text 	s have been adapted to	the new compan	y name where appropriate.
••			a sheet
19990801	Product specification	-	PSMN070-200_SERIES_HG v.2
	20101214 • The forma guidelines • Legal text • Type num	 The format of this data sheet has guidelines of NXP Semiconductor Legal texts have been adapted to Type number PSMN070-200B se PSMN070-200_SERIES_HG v.3. 	 20101214 Product data sheet - The format of this data sheet has been redesigned guidelines of NXP Semiconductors. Legal texts have been adapted to the new company Type number PSMN070-200B separated from data PSMN070-200_SERIES_HG v.3.

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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